| Type | L # | Hits | Search Text | DBs | Time Stamp | Comments | Error Definition | Errors |
|------|-----|------|-------------|-----|------------|----------|------------------|--------|
| 1 IS&R | L6 | 5 | (("6043157") or ("6087231") or ("6083836") or ("5266519") or ("6475908")).PN. | USPAT; US-PGPUB | 2004/07/08 17:06 | | 0 | |
| 2 IS&R | L7 | 1 | ("6750519").PN. | USPAT; US-PGPUB | 2004/07/08 17:20 | | 0 | |
| 3 IS&R | L8 | 1 | ("6677652").PN. | USPAT; US-PGPUB | 2004/07/08 18:30 | | 0 | |
| 4 BRS | L9 | 5473 | differen$4 with (oxygen or O2 or "O2" or "O.sub.2" or oxide or oxides) with concentration$1 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/08 19:24 | | 0 | |
| 5 BRS | L10 | 106203 | CMOS or "CMOS" | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/08 18:33 | | 0 | |
| 6 BRS | L11 | 82120 | NMOS$4 or N-MOS$4 or (N adj3 MOS$4) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/08 18:33 | | 0 | |

| | Type | L # | Hits | Search Text | DBs | Time Stamp | Comments | Error Definition | Errors |
|---|---|---|---|---|---|---|---|---|---|
| 7 | BRS | L12 | 66079 | PMOS$4 or P-MOS$4 or EPO; JPO; (P adj3 MOS$4) | USPAT; US-PGPUB; DERWENT; IBM_TDB | 2004/07/08 18:34 | | | 0 |
| 8 | BRS | L13 | 133038 | 10 or (11 and 12) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/08 18:34 | | | 0 |
| 9 | BRS | L14 | 21484 | metal adj5 gate$1 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/08 18:58 | | | 0 |
| 10 | BRS | L15 | 33191 | work$3 near3 function$1 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/08 18:35 | | | 0 |
| 11 | BRS | L16 | 10 | 9 and 13 and 14 and 15 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/08 18:36 | | | 0 |
| 12 | BRS | L17 | 7241 | conduct$5 adj oxide$1 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/08 18:47 | | | 0 |

| Type | L # | Hits | Search Text | DBs | Time Stamp | Comments | Error Definition | Errors |
|---|---|---|---|---|---|---|---|---|
| 13 BRS | L18 | 139 | metal adj oxide adj gate$1 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/08 18:47 | | | 0 |
| 14 BRS | L19 | 1644014 | ruthenium or Ru or Iridium or Ir or Osmium or Os or Rhodium or Rh or Rhenium or Re | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/08 18:48 | | | 0 |
| 15 BRS | L20 | 2 | conduct$5 adj oxide adj gate$1 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/08 18:50 | | | 0 |
| 16 BRS | L21 | 35882 | (implant$8 or inject$4 or dop$5) near15 (oxygen or O2 or "O2" or "O.sub.2") | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/08 19:14 | | | 0 |
| 17 BRS | L22 | 59 | 13 and (14 or 17 or 18 or 20) and 15 and 21 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/08 18:55 | | | 0 |
| 18 BRS | L23 | 6 | 22 and 9 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/08 18:55 | | | 0 |

| Type | L # | Hits | Search Text | DBs | Time Stamp | Comments | Error Definition | Errors |
|------|-----|------|-------------|-----|------------|----------|------------------|--------|
| 19 BRS | L24 | 61576 | (metal or 19) near15 gate$1 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/08 18:59 | | | 0 |
| 20 BRS | L25 | 3756 | (implant$8 or inject$4 or dop$5) with (oxygen or O2 or "O2" or "O.sub.2") with (19 or metal$2) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/08 19:17 | | | 0 |
| 21 BRS | L26 | 314 | (24 or 20 or 18 or 17) and 25 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/08 19:18 | | | 0 |
| 22 BRS | L27 | 32 | 26 and 15 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/08 19:19 | | | 0 |
| 23 BRS | L28 | 10792 | (differen$4 or var$6 or dissimilar$4 or divers$6) with (oxygen or O2 or "O2" or "O.sub.2" or oxide or oxides) with concentration$1 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/08 19:27 | | | 0 |

| Type | L # | Hits | Search Text | DBs | Time Stamp | Comments | Error Definition | Errors |
|---|---|---|---|---|---|---|---|---|
| BRS | L29 | 45 | 28 and (24 or 20 or 18 or 17 or 14) and 15 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/08 19:29 | | | 0 |

24

| L Number | Hits | Search Text | DB | Time stamp |
|---|---|---|---|---|
| 6 | 5 | (("6043157") or ("6087231") or ("6083836") or ("5266519") or ("6475908")).PN. | USPAT; US-PGPUB | 2004/07/08 17:06 |
| 7 | 1 | ("6750519").PN. | USPAT; US-PGPUB | 2004/07/08 17:20 |
| 8 | 1 | ("6677652").PN. | USPAT; US-PGPUB | 2004/07/08 18:30 |
| 9 | 5473 | differen$4 with (oxygen or O2 or "O2" or "O.sub.2" or oxide or oxides) with concentration$1 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/08 19:24 |
| 10 | 106203 | CMOS or "CMOS" | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/08 18:33 |
| 11 | 82120 | NMOS$4 or N-MOS$4 or (N adj3 MOS$4) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/08 18:33 |
| 12 | 66079 | PMOS$4 or P-MOS$4 or (P adj3 MOS$4) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/08 18:34 |
| 13 | 133038 | (CMOS or "CMOS") or ((NMOS$4 or N-MOS$4 or (N adj3 MOS$4)) and (PMOS$4 or P-MOS$4 or (P adj3 MOS$4))) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/08 18:34 |
| 14 | 21484 | metal adj5 gate$1 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/08 18:58 |
| 15 | 33191 | work$3 near3 function$1 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/08 18:35 |
| 16 | 10 | (differen$4 with (oxygen or O2 or "O2" or "O.sub.2" or oxide or oxides) with concentration$1) and ((CMOS or "CMOS") or ((NMOS$4 or N-MOS$4 or (N adj3 MOS$4)) and (PMOS$4 or P-MOS$4 or (P adj3 MOS$4)))) and (metal adj5 gate$1) and (work$3 near3 function$1) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/08 18:36 |
| 17 | 7241 | conduct$5 adj oxide$1 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/08 18:47 |
| 18 | 139 | metal adj oxide adj gate$1 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/08 18:47 |
| 19 | 1644014 | ruthenium or Ru or Iridium or Ir or Osmium or Os or Rhodium or Rh or Rhenium or Re | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/08 18:48 |

C:\APPS\east\workspaces\10227697.wsp

| | | | | |
|---|---|---|---|---|
| 20 | 2 | conduct$5 adj oxide adj gate$1 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/08 18:50 |
| 21 | 35882 | (implant$8 or inject$4 or dop$5) near15 (oxygen or O2 or "O2" or "O.sub.2") | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/08 19:14 |
| 22 | 59 | ((CMOS or "CMOS") or ((NMOS$4 or N-MOS$4 or (N adj3 MOS$4)) and (PMOS$4 or P-MOS$4 or (P adj3 MOS$4)))) and ((metal adj5 gate$1) or (conduct$5 adj oxide$1) or (metal adj oxide adj gate$1) or (conduct$5 adj oxide adj gate$1)) and (work$3 near3 function$1) and ((implant$8 or inject$4 or dop$5) near15 (oxygen or O2 or "O2" or "O.sub.2")) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/08 18:55 |
| 23 | 6 | (((CMOS or "CMOS") or ((NMOS$4 or N-MOS$4 or (N adj3 MOS$4)) and (PMOS$4 or P-MOS$4 or (P adj3 MOS$4)))) and ((metal adj5 gate$1) or (conduct$5 adj oxide$1) or (metal adj oxide adj gate$1) or (conduct$5 adj oxide adj gate$1)) and (work$3 near3 function$1) and ((implant$8 or inject$4 or dop$5) near15 (oxygen or O2 or "O2" or "O.sub.2"))) and (differen$4 with (oxygen or O2 or "O2" or "O.sub.2" or oxide or oxides) with concentration$1) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/08 18:55 |
| 24 | 61576 | (metal or (ruthenium or Ru or Iridium or Ir or Osmium or Os or Rhodium or Rh or Rhenium or Re)) near15 gate$1 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/08 18:59 |
| 25 | 3756 | (implant$8 or inject$4 or dop$5) with (oxygen or O2 or "O2" or "O.sub.2") with ((ruthenium or Ru or Iridium or Ir or Osmium or Os or Rhodium or Rh or Rhenium or Re) or metal$2) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/08 19:17 |
| 26 | 314 | (((metal or (ruthenium or Ru or Iridium or Ir or Osmium or Os or Rhodium or Rh or Rhenium or Re)) near15 gate$1) or (conduct$5 adj oxide adj gate$1) or (metal adj oxide adj gate$1) or (conduct$5 adj oxide$1)) and ((implant$8 or inject$4 or dop$5) with (oxygen or O2 or "O2" or "O.sub.2") with ((ruthenium or Ru or Iridium or Ir or Osmium or Os or Rhodium or Rh or Rhenium or Re) or metal$2)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/08 19:18 |
| 27 | 32 | ((((metal or (ruthenium or Ru or Iridium or Ir or Osmium or Os or Rhodium or Rh or Rhenium or Re)) near15 gate$1) or (conduct$5 adj oxide adj gate$1) or (metal adj oxide adj gate$1) or (conduct$5 adj oxide$1)) and ((implant$8 or inject$4 or dop$5) with (oxygen or O2 or "O2" or "O.sub.2") with ((ruthenium or Ru or Iridium or Ir or Osmium or Os or Rhodium or Rh or Rhenium or Re) or metal$2))) and (work$3 near3 function$1) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/08 19:19 |
| 28 | 10792 | (differen$4 or var$6 or dissimilar$4 or divers$6) with (oxygen or O2 or "O2" or "O.sub.2" or oxide or oxides) with concentration$1 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/08 19:27 |
| 29 | 45 | ((differen$4 or var$6 or dissimilar$4 or divers$6) with (oxygen or O2 or "O2" or "O.sub.2" or oxide or oxides) with concentration$1) and (((metal or (ruthenium or Ru or Iridium or Ir or Osmium or Os or Rhodium or Rh or Rhenium or Re)) near15 gate$1) or (conduct$5 adj oxide adj gate$1) or (metal adj oxide adj gate$1) or (conduct$5 adj oxide$1) or (metal adj5 gate$1)) and (work$3 near3 function$1) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/08 19:29 |
| - | 94396 | CMOS | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/08 18:32 |

| - | 73476 | NMOS$4 or N-MOS$4 or (N adj3 MOS$4) | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/07/08 18:33 |
|---|---|---|---|---|
| - | 58888 | PMOS$4 or P-MOS$4 or (P adj3 MOS$4) | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/07/08 18:33 |
| - | 18924 | metal adj5 gate$1 | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/07/08 18:34 |
| - | 29246 | work$3 near3 function$1 | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/07/08 18:35 |
| - | 118169 | CMOS or ((NMOS$4 or N-MOS$4 or (N adj3 MOS$4)) and (PMOS$4 or P-MOS$4 or (P adj3 MOS$4))) | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/30 16:53 |
| - | 432 | (metal adj5 gate$1) and (work$3 near3 function$1) and (CMOS or ((NMOS$4 or N-MOS$4 or (N adj3 MOS$4)) and (PMOS$4 or P-MOS$4 or (P adj3 MOS$4)))) | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/27 15:30 |
| - | 95937 | CMOS or "CMOS" or (complementary adj metal adj oxide adj (semiconduct$4 or silicon)) | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/30 16:53 |
| - | 73591 | NMOS$4 or N-MOS$4 or (N adj3 MOS$4) | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/30 16:54 |
| - | 58981 | PMOS$4 or P-MOS$4 or (P adj3 MOS$4) | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/30 16:54 |
| - | 119584 | (CMOS or "CMOS" or (complementary adj metal adj oxide adj (semiconduct$4 or silicon))) or ((NMOS$4 or N-MOS$4 or (N adj3 MOS$4)) and (PMOS$4 or P-MOS$4 or (P adj3 MOS$4))) | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/30 16:55 |
| - | 31830 | work$3 near3 function$3 | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/30 16:56 |
| - | 6415 | conduct$5 adj oxide$1 | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/07/08 18:47 |

| | | | | |
|---|---:|---|---|---|
| - | 106 | metal adj oxide adj gate$1 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/08 18:47 |
| - | 8 | (((CMOS or "CMOS" or (complementary adj metal adj oxide adj (semiconduct$4 or silicon))) or ((NMOS$4 or N-MOS$4 or (N adj3 MOS$4)) and (PMOS$4 or P-MOS$4 or (P adj3 MOS$4)))) and (work$3 near3 function$3) and (metal adj oxide adj gate$1) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/09/30 16:57 |
| - | 14 | 6027961.URPN. | USPAT | 2003/09/30 17:06 |
| - | 3 | 6365450.URPN. | USPAT | 2003/09/30 17:39 |
| - | 4 | ("5966597" \| "6033963" \| "6087208" \| "6087231").PN. | USPAT | 2003/09/30 17:41 |
| - | 5 | ("4605947" \| "5268590" \| "5457580" \| "5600169" \| "5923999").PN. | USPAT | 2003/09/30 17:42 |
| - | 1455017 | ruthenium or Ru or Iridium or Ir or Osmium or Os or Rhodium or Rh or Rhenium or Re | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/08 18:48 |
| - | 16402 | (ruthenium or Ru or Iridium or Ir or Osmium or Os or Rhodium or Rh or Rhenium or Re) and ((CMOS or "CMOS" or (complementary adj metal adj oxide adj (semiconduct$4 or silicon))) or ((NMOS$4 or N-MOS$4 or (N adj3 MOS$4)) and (PMOS$4 or P-MOS$4 or (P adj3 MOS$4)))) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/09/30 18:39 |
| - | 631 | (work$3 near3 function$3) and ((ruthenium or Ru or Iridium or Ir or Osmium or Os or Rhodium or Rh or Rhenium or Re) and ((CMOS or "CMOS" or (complementary adj metal adj oxide adj (semiconduct$4 or silicon))) or ((NMOS$4 or N-MOS$4 or (N adj3 MOS$4)) and (PMOS$4 or P-MOS$4 or (P adj3 MOS$4))))) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/09/30 18:40 |
| - | 102 | (ruthenium or Ru or Iridium or Ir or Osmium or Os or Rhodium or Rh or Rhenium or Re) with (NMOS$4 or N-MOS$4 or (N adj3 MOS$4)) with (gate$1 or electrode$1) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/09/30 18:41 |
| - | 5 | ((work$3 near3 function$3) and ((ruthenium or Ru or Iridium or Ir or Osmium or Os or Rhodium or Rh or Rhenium or Re) and ((CMOS or "CMOS" or (complementary adj metal adj oxide adj (semiconduct$4 or silicon))) or ((NMOS$4 or N-MOS$4 or (N adj3 MOS$4)) and (PMOS$4 or P-MOS$4 or (P adj3 MOS$4))))))) and ((ruthenium or Ru or Iridium or Ir or Osmium or Os or Rhodium or Rh or Rhenium or Re) with (NMOS$4 or N-MOS$4 or (N adj3 MOS$4)) with (gate$1 or electrode$1)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/09/30 18:41 |
| - | 4742 | metal adj gate$1 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/09/30 18:47 |
| - | 29 | (metal adj oxide adj gate$1) and (metal adj gate$1) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/09/30 18:47 |
| - | 2 | conduct$5 adj oxide adj gate$1 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/08 18:48 |
| - | 5 | (((ruthenium or Ru or Iridium or Ir or Osmium or Os or Rhodium or Rh or Rhenium or Re) with (NMOS$4 or N-MOS$4 or (N adj3 MOS$4)) with (gate$1 or electrode$1)) and ((CMOS or "CMOS" or (complementary adj metal adj oxide adj (semiconduct$4 or silicon))) or ((NMOS$4 or N-MOS$4 or (N adj3 MOS$4)) and (PMOS$4 or P-MOS$4 or (P adj3 MOS$4))))) and (work$3 near3 function$3) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/09/30 19:24 |

| - | 89 | ((ruthenium or Ru or Iridium or Ir or Osmium or Os or Rhodium or Rh or Rhenium or Re) with (NMOS$4 or N-MOS$4 or (N adj3 MOS$4)) with (gate$1 or electrode$1)) and ((CMOS or "CMOS" or (complementary adj metal adj oxide adj (semiconduct$4 or silicon))) or ((NMOS$4 or N-MOS$4 or (N adj3 MOS$4)) and (PMOS$4 or P-MOS$4 or (P adj3 MOS$4)))) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/09/30 19:24 |
|---|---|---|---|---|
| - | 6778 | (ruthenium or Ru or Iridium or Ir or Osmium or Os or Rhodium or Rh or Rhenium or Re) near15 gate$1 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/09/30 19:33 |
| - | 1225 | (((CMOS or "CMOS" or (complementary adj metal adj oxide adj (semiconduct$4 or silicon))) or ((NMOS$4 or N-MOS$4 or (N adj3 MOS$4)) and (PMOS$4 or P-MOS$4 or (P adj3 MOS$4)))) and ((ruthenium or Ru or Iridium or Ir or Osmium or Os or Rhodium or Rh or Rhenium or Re) near15 gate$1) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/09/30 19:34 |
| - | 75 | (work$3 near3 function$3) and (((CMOS or "CMOS" or (complementary adj metal adj oxide adj (semiconduct$4 or silicon))) or ((NMOS$4 or N-MOS$4 or (N adj3 MOS$4)) and (PMOS$4 or P-MOS$4 or (P adj3 MOS$4)))) and ((ruthenium or Ru or Iridium or Ir or Osmium or Os or Rhodium or Rh or Rhenium or Re) near15 gate$1)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/09/30 19:34 |
| - | 44 | (metal adj oxide adj gate$1) and ((CMOS or "CMOS" or (complementary adj metal adj oxide adj (semiconduct$4 or silicon))) or ((NMOS$4 or N-MOS$4 or (N adj3 MOS$4)) and (PMOS$4 or P-MOS$4 or (P adj3 MOS$4)))) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/09/30 20:01 |